

Magnetism and Electronic Structure in ZnFe_2O_4 and MnFe_2O_4

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Density functional calculations are used to study magnetic and electronic properties of the spinel ferrites, ZnFe_2O_4 and MnFe_2O_4 . Correct magnetic orderings are obtained. ZnFe_2O_4 is predicted to be a small gap insulator in agreement with experiment. MnFe_2O_4 is found to be a low carrier density half-metal in the fully ordered state. However, strong effects on the electronic structure are found upon partial interchange of Fe and Mn atoms. This indicates that the insulating character may be due to Anderson localization associated with the intersite Mn-Fe disorder.

Spinel structure ferrites play an important role in technologies because a large subset of these materials are room temperature, insulating ferromagnets. While the basic physics underlying the magnetic orderings has been understood since the work of Goodenough and co-workers,^{1,2} a fundamental predictive understanding of issues like gap formation is not yet well established. Here we report density functional calculations of the electronic structure of ZnFe_2O_4 and MnFe_2O_4 , focussing mainly on the latter. MnFe_2O_4 differs from ZnFe_2O_4 in an important aspect. As prepared, it invariably has significant disorder between the Mn and Fe sites.³ This intersite disorder amounts to approximately 20% Fe on the Mn site in normally prepared stoichiometric samples. This disorder has caused some confusion both in the analysis of the dependence of magnetic properties on sample size⁴⁻⁷ and in understanding the temperature dependence of transport quantities.^{8,9} MnFe_2O_4 is insulating. Small gap values from 0.04 – 0.06 eV (Ref. 7) have been extracted from transport data determined from eddy currents.

In the generalized gradient approximation (GGA),¹⁰ a small insulating gap, consistent with experiment, is found in ZnFe_2O_4 , while ideal stoichiometric MnFe_2O_4 predicted to be a low carrier density half-metal. However, total energy calculations show that partial inversion is strongly favored in MnFe_2O_4 so the ideal ordered phase cannot be made, at least not by standard methods. The calculations show a strong enough coupling of the electronic states near the Fermi level E_F to intersite cation disorder in MnFe_2O_4 to exceed the criterion for Anderson localization in this material. We propose that this may underlie the insulating behavior of MnFe_2O_4 , and note that it is consistent with a number of experimental observations, like the difficulty in determining gap values spectroscopically, and the variation in the transport gap with temperature and sample preparation.

Our results were obtained using well converged linearized augmented planewave (LAPW) calculations.¹¹ Details are given in our prior paper, where some results

for ZnFe_2O_4 are reported.¹² There, we found that the electronic structure is highly sensitive to the structural parameters used, particularly, the internal O coordinate u of the spinel structure. For ZnFe_2O_4 we used the experimental value determined from structural refinements. MnFe_2O_4 has not been made in non-inverted form, so we instead used total energy minimization. In this way we obtained $u=0.381$ and $a=8.49\text{\AA}$. With these and no inversion, we find the ferrimagnetic state to be the ground state. Specifically, we did total energy calculations for the ferrimagnetic state, a ferromagnetic state and antiferromagnetic A and B sublattices. The ferrimagnetic configuration was lowest in energy, *e.g.* by 2.03 eV per cell (2 Mn and 4 Fe ions) relative to the ferromagnetic. Details will be given in a longer report.¹³

In an ionic model, Fe has a trivalent high spin d^5 configuration, while both Zn and Mn are divalent, so Mn is also d^5 . We find a spin magnetization of exactly $10 \mu_B$ per unit cell in the ferrimagnetic state, as in the ionic model. As seen in the band structure (Fig. 1), this is due to a half-metallic state. The density of states (DOS) and projections (Fig. 2) show that the ionic model is followed, though there is some reduction in moments due to hybridization. There is a majority spin gap but only a pseudogap in the minority channel. The majority channel is described by the ionic model. It has O $2p$ bands from ~ -8 eV (relative to the Fermi energy, E_F) to ~ -3 eV. Fe t_{2g} bands overlap the top of these and extend to -2.3 eV. These are separated by a clean crystal field gap from an Fe e_g manifold, which goes from -1.5 to -0.2 eV. The unoccupied Mn d bands are above $+2$ eV and show a smaller tetrahedral crystal field with overlapping e_g and t_{2g} manifolds. As mentioned, the minority spin channel is metallic. This is a result of a manifold of 22 bands lying between -2 eV and 1 eV (Fig. 3). The lower part of this manifold (from -2 to -1 eV) is from 4 Mn e_g bands, which are below the t_{2g} bands in the Mn tetrahedral crystal field. The next set (of 6), extending to E_F , is Mn t_{2g} derived, while the remaining 12 bands are from

the Fe t_{2g} . There is a pseudogap at E_F . This separates the Mn t_{2g} and Fe t_{2g} states. The states at E_F come from the overlap of a two fold degenerate band that disperses downwards from 0.4 eV at Γ with two singly degenerate bands starting just below E_F at Γ and dispersing upwards. The upward dispersing bands (from Γ) come from Fe d states, while the downward dispersing band is Mn derived. The downwards (hole) and upwards (electron) bands cross very close to E_F on the Γ -X line. Their anti-crossing is sufficiently strong that a true gap opens up between them along the other symmetry lines (see *e.g.* the Γ -L line. The result is a semimetallic half-metal, with a large band gap over 2 eV in the majority channel and small electron and hole Fermi surfaces along the Γ -X direction in the minority channel.

The calculated band structure needs to be reconciled with the experimentally observed insulating nature of MnFe_2O_4 . For this we focus on the region near E_F , which is relevant to transport. We calculated the band structure with the experimental crystal structure, but still having no inversion. This amounts to an oxygen shift of 0.06 Å and a very slight lattice expansion. With this shift, the band topology changes because of a 0.3 eV upwards shift of the (previously) first occupied band from E_F in the calculated structure. This Fe derived band then becomes unoccupied at Γ and the smaller electron Fermi surface is removed while a new hole surface is introduced due to the strong downwards dispersion of this band along Γ -L. The value of u for the experimental structure is an average diffraction value for a disordered crystal. Presumably, the main contribution to the shift in u is the difference in ionic radii of Mn and Fe, which is a local effect. As such, it is reasonable to suppose that the local static variation in the oxygen positions in the disordered material will be at least as large. With this, band shifts larger than the effective E_F of the hole and electron pockets should be present. This is the criterion for Anderson localization. Furthermore, in addition to band shifts due to O relaxation around intersite defects, there will be a contribution due to the different ionic potential of the anti-site species. Here this is the stronger effect. To qualitatively characterize the changes in ionic potential, we did calculations with the MnFe_2O_4 structure, but with one or two Fe atoms interchanged with Mn in the unit cell (containing 4 Fe and 2 Mn atoms). These interchanges strongly modify the electronic structure near E_F . For example, interchanging a single Fe-Mn pair in the unit cell destroys the half-metallic electronic structure by introducing a narrow majority spin peak derived mostly from the d electrons of the B -site Mn atom at E_F . Meanwhile, the minority spin bands are shifted so that the pseudogap at E_F becomes a true gap, though because of the majority occupation it is shifted to slightly (0.2 eV) below E_F . With both Mn on the B -sublattice, this minority gap is further opened up to 0.6 eV. The shifts in band edge electronic states are clearly well above the threshold for Anderson localization.

Here, we froze the atomic positions at the structure

for non-inverted MnFe_2O_4 , thus neglecting relaxation around the anti-site defect. Even so, the calculated total energies for the partially inverted cells were lower than for the ideal structure; we get an energy lowering of 8 mRy per Mn for a single interchange and 12 mRy per Mn for a double interchange. While the neglected relaxation is no doubt important it can only raise these energy differences (further disfavoring the non-inverted state). Presumably, a large ingredient in the relaxation will be a competition between neighboring metal atoms for metal-oxygen bond lengths. This interaction will be repulsive between neighboring antisites, and if strong enough may limit the amount of inversion. In any case, the calculated energetics mean that at least partial inversion is energetically favored in MnFe_2O_4 with a rather high energy scale (at least 8 mRy per pair *i.e.* $> 1250\text{K}$), so we conclude that it is not possible to make non-inverted MnFe_2O_4 by equilibrium methods at accessible temperatures. This is unfortunate since our results show that if it could be made and the insulating gap is really due to Anderson localization, then non-inverted MnFe_2O_4 would be a low carrier density half-metal with a Curie temperature well above room temperature, and therefore of interest for spintronic applications. One may speculate that epitaxial growth, with strain, may favor different inversion levels. Perhaps under suitable conditions this can be exploited to grow films that are not inverted at least near an interface – a possibility that deserves experimental study.

It seems plausible that this Anderson localization mechanism for insulating behavior may be operative in MnFe_2O_4 . If so, localized states should exist in the gap region around E_F . These may be observable thermodynamically and spectroscopically. Also, the effective value of the insulating gap will be sensitive to the strength of the disorder. Of course, it is possible that the insulating nature of MnFe_2O_4 is due to Hubbard correlations. Though the behavior of the kind of multi-site, multi-band Hubbard type model that would be needed to describe MnFe_2O_4 is no doubt complex, band shifts controlled by U or $U - \Delta$, where Δ is the onsite LSDA Hund's exchange splitting, may be expected. It seems that in this case gaps too large compared to experiment may be expected. It will be of interest to measure thermodynamic and spectroscopic properties of MnFe_2O_4 with various levels of inversion to shed light on this issue.

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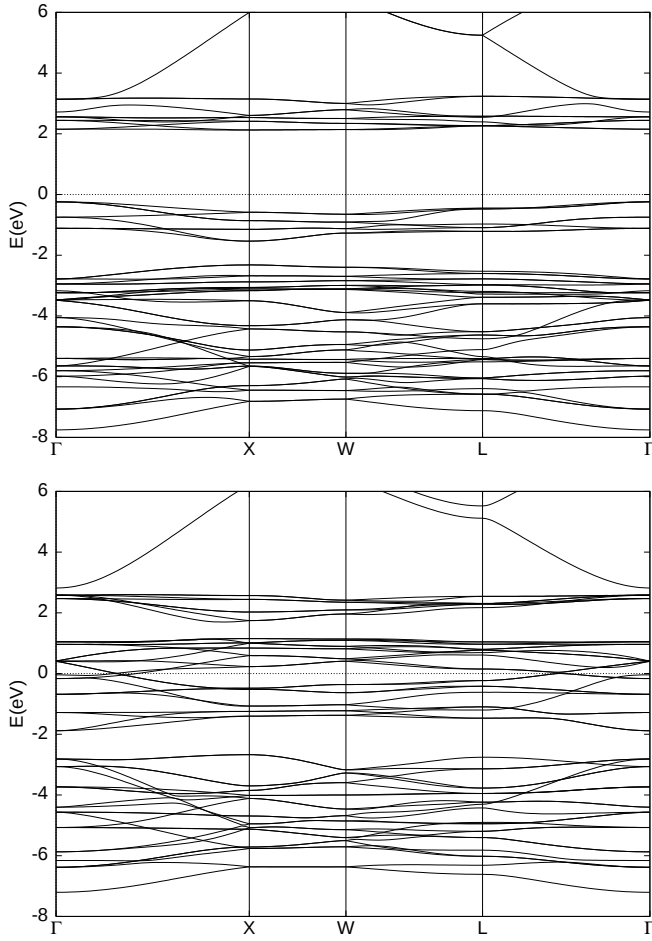


FIG. 1. Band structure of ferrimagnetic MnFe_2O_4 . E_F is at 0. Note the half-metallic gap at E_F in the majority (top panel) but not in the minority (bottom panel).

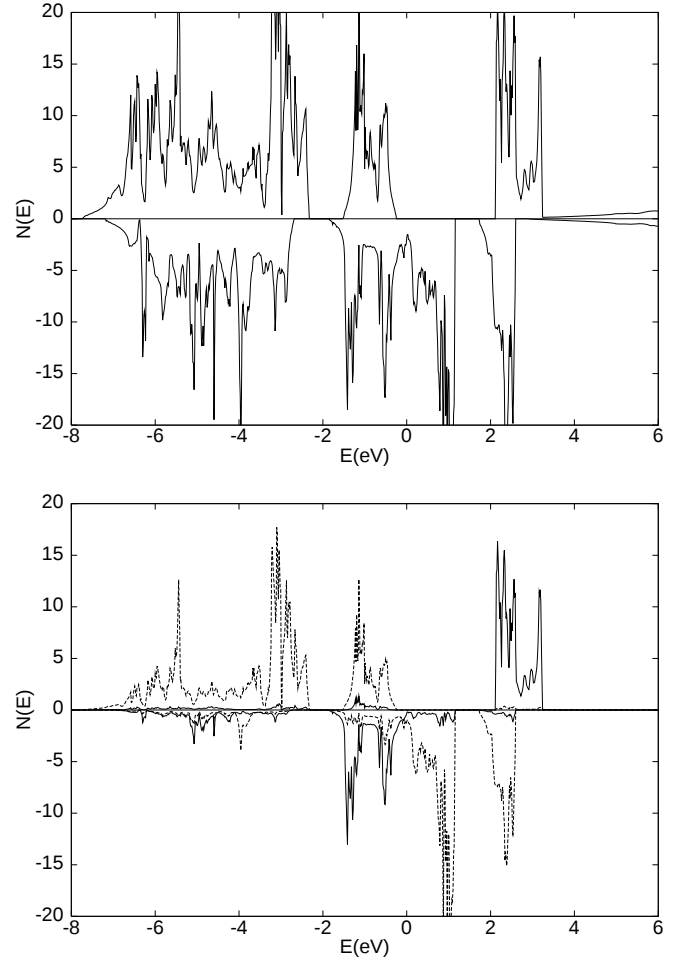


FIG. 2. Electronic DOS corresponding to Fig. 1 (top), and projections onto the Mn (solid) and Fe (dashed) LAPW spheres (bottom). The majority spin is shown above the axis and the minority below.

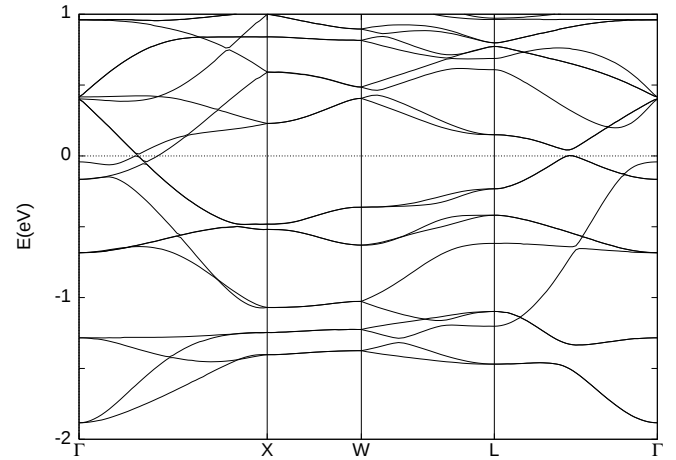


FIG. 3. Blowup around E_F of the minority spin band structure as in Fig. 1.